



DACO SEMICONDUCTOR CO., LTD.

DACSB400120CT

SiC SCHOTTKY DIODE TYPE 2x200A

Features

- High surge current capable
- Zero reverse recovery current
- High bandwidth
- Temperature Independent Switching Behavior
- V_{DC} 1200 V
- I_F (T_C<135°C) 2x200 A

Benefits

- Unipolar rectifier
- Zero switching loss
- Higher efficiency
- Smaller heat sink
- Parallel devices without thermal runaway

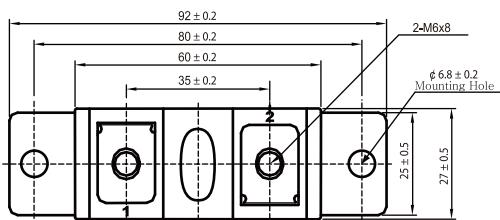
Applications

- Motor drives
- Switch mode power supplies
- EV chargers
- Solar inverters
- Welding equipment
- Power factor correction
- Diode snubber
- Automotive
- Induction heating

Preliminary



Dimensions in mm (1 mm = 0.0394")



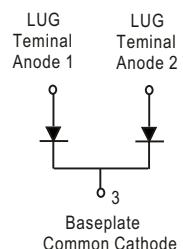
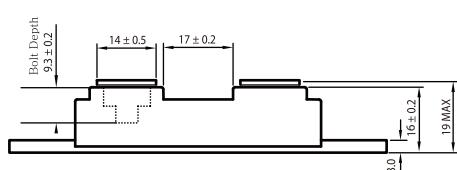
Maximum Ratings

Operating Junction Temperature : -55 °C to +175 °C

Storage Temperature : -55 °C to +175 °C

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum DC Blocking Voltage
DACSB400120CT	1200V	1200V

Maximum Rating	Symbol	Conditions	Value	Unit
Continuous forward current (per leg)	I _F	T _C =135 °C	200	
Surge non-repetitive forward current sine halfwave (per leg)	I _{FSM}	T _C =25 °C, t _p =8.3 ms	1600	A
		T _C =150 °C, t _p =8.3 ms	1000	
Non-repetitive peak forward current (per leg)	I _{F,max}	T _C =25 °C, t _p =10 μs	6400	
		T _C =150 °C, t _p =10 μs	4000	
Repetitive peak reverse voltage	V _{RRM}	T _J =25 °C	1200	V
Mounting torque		M6 Screw	3~4.7	N-m





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Electrical Characteristics, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified. (per leg)

Static Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
DC blocking voltage	V_{DC}		1,200	-	-	V
Diode forward voltage	V_F	$I_F = 25A, T_j = 25\text{ }^\circ\text{C}$	-	1.6	1.8	
		$I_F = 25A, T_j = 175\text{ }^\circ\text{C}$	-	2.4	2.9	
Reverse current	I_R	$V_R = 1,200V, T_j = 25\text{ }^\circ\text{C}$	-	10	130	μA
		$V_R = 1,200V, T_j = 175\text{ }^\circ\text{C}$	-	140	1,400	

AC Characteristics (per leg)

Static Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Total capacitive charge	Q_{rr}	$V_R=1,200V, T_j=25\text{ }^\circ\text{C}$	-	617	-	nC
Total capacitance	C	$V_R=0V, f=1\text{ MHz}$ $T_j=25\text{ }^\circ\text{C}$	-	11,120	-	pF
		$V_R=600V, f=1\text{ MHz}$ $T_j=25\text{ }^\circ\text{C}$	-	1,104	-	
		$V_R=1,000V, f=1\text{ MHz}$ $T_j=25\text{ }^\circ\text{C}$	-	1,034	-	

Thermal Characteristics (per leg)

Static Characteristics	Symbol	Values		Unit
		typ.		
Thermal resistance from junction to case	$R_{\theta JC}$	0.07	$^\circ\text{C/W}$	

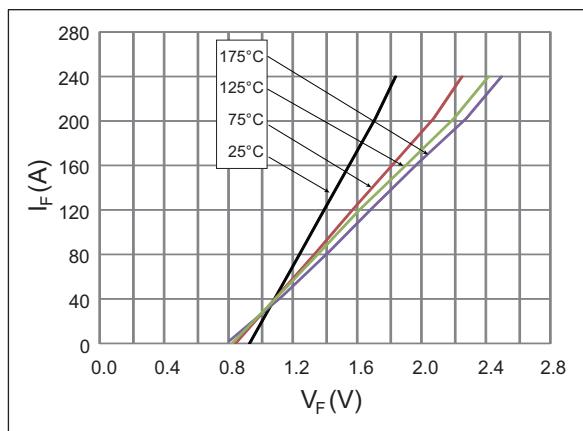


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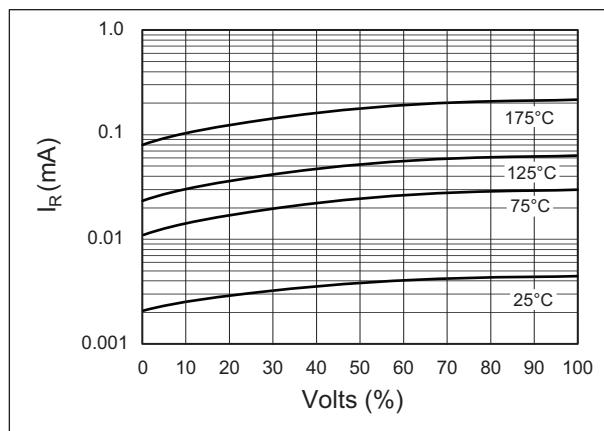
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Typical Performance

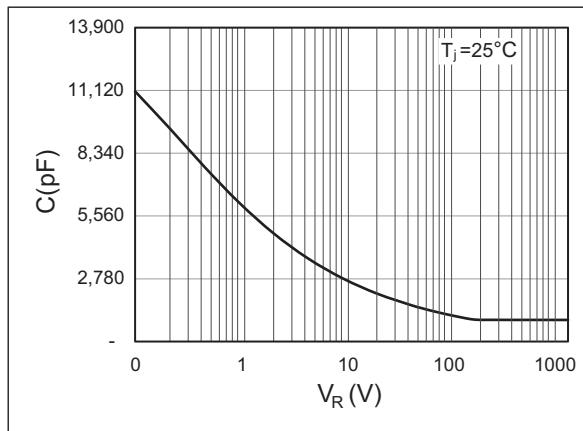
Forward Characteristics (parameterized on T_j)



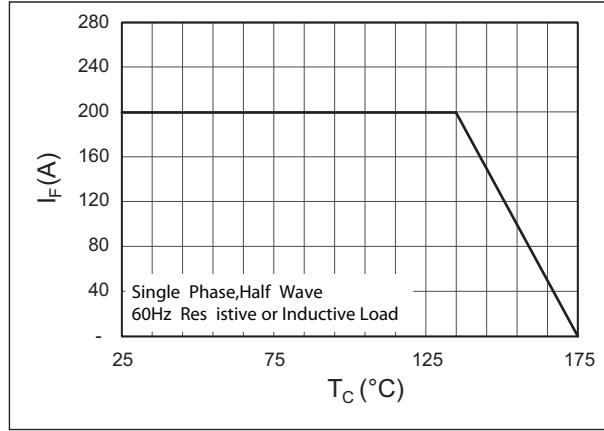
Reverse Characteristics (parameterized on T_j)



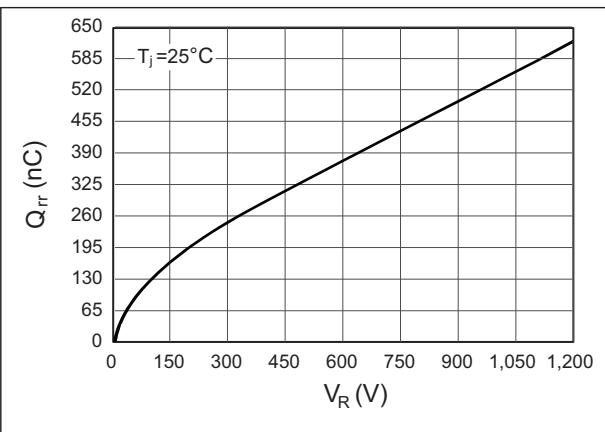
Capacitance



Current Derating



Recovery Charge



Forward Surge Current

